



1200 V  
Size 2  
Ultra Fast Speed  
Short Circuit Rated  
6" Wafer

## Electrical Characteristics ( Wafer Form )

| Parameter     | Description                             | Guaranteed (Min/Max) | Test Conditions                                           |
|---------------|-----------------------------------------|----------------------|-----------------------------------------------------------|
| $V_{CE(on)}$  | Collector-to-Emitter Saturation Voltage | 4.5V Max.            | $I_C = 5.5A$ , $T_J = 25^\circ C$ , $V_{GE} = 15V$        |
| $V_{(BR)CES}$ | Collector-to-Emitter Breakdown Voltage  | 1200V Min.           | $T_J = 25^\circ C$ , $I_{CES} = 250\mu A$ , $V_{GE} = 0V$ |
| $V_{GE(th)}$  | Gate Threshold Voltage                  | 3.0V Min., 6.0V Max. | $V_{GE} = V_{CE}$ , $T_J = 25^\circ C$ , $I_C = 250\mu A$ |
| $I_{CES}$     | Zero Gate Voltage Collector Current     | 300 $\mu A$ Max.     | $T_J = 25^\circ C$ , $V_{CE} = 1200V$                     |
| $I_{GES}$     | Gate-to-Emitter Leakage Current         | $\pm 11 \mu A$ Max.  | $T_J = 25^\circ C$ , $V_{GE} = \pm 20V$                   |

## Mechanical Data

|                                              |                                                                               |
|----------------------------------------------|-------------------------------------------------------------------------------|
| Norminal Backmetal Composition, Thickness:   | Cr-Ni / V-Ag ( 1kA-2kA-.2.5kA )                                               |
| Norminal Front Metal Composition, Thickness: | 99% Al, 1% Si (4 microns)                                                     |
| Dimensions:                                  | 0.112" x 0.150"                                                               |
| Wafer Diameter:                              | 150mm, with std. < 100 > flat                                                 |
| Wafer thickness:                             | .015" + / -.003"                                                              |
| Relevant Die Mechanical Dwg. Number          | 01-5266                                                                       |
| Minimum Street Width                         | 100 Microns                                                                   |
| Reject Ink Dot Size                          | 0.25mm Diameter Minimum                                                       |
| Ink Dot Location                             | Consistent throughout same wafer lot                                          |
| Recommended Storage Environment:             | Store in original container, in dessicated nitrogen, with no contamination    |
| Recommended Die Attach Conditions            | For optimum electrical results, die attach temperature should not exceed 300C |

Reference Standard IR packaged part ( for design ) : IRG4PH20K (When available)

## Die Outline

